

FSB70550

Motion SPM® 7 Series

Features

- UL Certified No. E209204 (UL1557)
- High Performance PQFN Package
- 500 V $R_{DS(on)} = 1.85 \Omega(\text{Max})$ FRFET MOSFET 3-Phase Inverter with Gate Drivers and Protection
- Separate Open-Source Pins from Low-Side MOSFETs for Three-Phase Current-Sensing
- Active-HIGH Interface, Works with 3.3 / 5 V Logic, Schmitt-trigger Input
- Optimized for Low Electromagnetic Interference
- HVIC Temperature-Sensing Built-In for Temperature Monitoring
- HVIC for Gate Driving with Under-Voltage Protection and Interlock Function
- Isolation Rating: 1500 V_{rms} / min.
- Moisture Sensitive Level (MSL) 3
- RoHS Compliant

Application

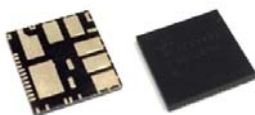
- 3-Phase Inverter Driver for Small Power AC Motor Drives

Related Source

- [AN-9077 - Motion SPM® 7 Series User's Guide](#)
- [AN-9078 - Surface Mount Guidelines for Motion SPM® 7 Series](#)

General Description

The FSB70550 is an advanced Motion SPM® 7 module providing a fully-featured, high-performance inverter output stage for AC Induction, BLDC and PMSM motors. These modules integrate optimized gate drive of the built-in MOSFETs (FRFET® technology) to minimize EMI and losses, while also providing multiple on-module protection features including under-voltage lockouts, thermal monitoring, fault reporting and interlock function. The built-in one HVIC translates the incoming logic-level gate inputs to the high-voltage, high-current drive signals required to properly drive the module's internal MOSFETs. Separate open-souce MOSFET terminals are available for each phase to support the widest variety of control algorithms.



Package Marking & Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FSB70550	FSB70550	PQFN27A	13"	24 mm	1000 units

Absolute Maximum Ratings

Inverter Part (each MOSFET unless otherwise specified.)

Symbol	Parameter	Conditions	Rating	Unit
V_{DSS}	Drain-Source Voltage of Each MOSFET		500	V
$*I_{D\ 25}$	Each MOSFET Drain Current, Continuous	$T_{CB} = 25^{\circ}\text{C}$ (1st Notes 1)	5.3	A
$*I_{D\ 80}$	Each MOSFET Drain Current, Continuous	$T_{CB} = 80^{\circ}\text{C}$	3.9	A
$*I_{DP}$	Each MOSFET Drain Current, Peak	$T_{CB} = 25^{\circ}\text{C}$, $PW < 100\ \mu\text{s}$	10.6	A
$*P_D$	Maximum Power Dissipation	$T_{CB} = 25^{\circ}\text{C}$, For Each MOSFET	110	W

Control Part (each HVIC unless otherwise specified.)

Symbol	Parameter	Conditions	Rating	Unit
V_{DD}	Control Supply Voltage	Applied Between V_{DD} and COM	20	V
V_{BS}	High-side Bias Voltage	Applied Between V_B and V_S	20	V
V_{IN}	Input Signal Voltage	Applied Between IN and COM	$-0.3 \sim V_{DD} + 0.3$	V
V_{FO}	Fault Output Supply Voltage	Applied Between FO and COM	$-0.3 \sim V_{DD} + 0.3$	V
I_{FO}	Fault Output Current	Sink Current FO Pin	5	mA
V_{CSC}	Current Sensing Input Voltage	Applied Between Csc and COM	$-0.3 \sim V_{DD} + 0.3$	V

Total System

Symbol	Parameter	Conditions	Rating	Unit
T_J	Operating Junction Temperature		$-40 \sim 150$	$^{\circ}\text{C}$
T_{STG}	Storage Temperature		$-40 \sim 125$	$^{\circ}\text{C}$
V_{ISO}	Isolation Voltage	60 Hz, Sinusoidal, 1 Minute, Connection Pins to Heat Sink Plate	1500	V_{rms}

1st Notes:

- T_{CB} is pad temperature of case bottom.
- Marking “*” is calculation value or design factor.

Electrical Characteristics ($T_J = 25^\circ\text{C}$, $V_{DD} = V_{BS} = 15\text{ V}$ unless otherwise specified.)**Inverter Part** (each MOSFET unless otherwise specified.)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
BV_{DSS}	Drain - Source Breakdown Voltage	$V_{IN} = 0\text{ V}$, $I_D = 1\text{ mA}$ (2nd Notes 1)	500	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{IN} = 0\text{ V}$, $V_{DS} = 500\text{ V}$	-	-	1	mA
$R_{DS(on)}$	Static Drain - Source Turn-On Resistance	$V_{DD} = V_{BS} = 15\text{ V}$, $V_{IN} = 5\text{ V}$, $I_D = 1.0\text{ A}$	-	1.6	1.85	Ω
V_{SD}	Drain - Source Diode Forward Voltage	$V_{DD} = V_{BS} = 15\text{ V}$, $V_{IN} = 0\text{ V}$, $I_D = -1.0\text{ A}$	-	0.9	1.2	V
t_{ON}	Switching Times	$V_{PN} = 300\text{ V}$, $V_{DD} = V_{BS} = 15\text{ V}$, $I_D = 1.0\text{ A}$ $V_{IN} = 0\text{ V} \leftrightarrow 5\text{ V}$, Inductive Load $L = 3\text{ mH}$ Low-Side MOSFET Switching (2nd Notes 2)	-	600	-	ns
$t_{D(ON)}$			-	540	-	ns
t_{OFF}			-	480	-	ns
$t_{D(OFF)}$			-	410	-	ns
I_{rr}			-	1.4	-	A
t_{rr}			-	90	-	ns
E_{ON}			-	45	-	μJ
E_{OFF}			-	7	-	μJ

Control Part (each HVIC unless otherwise specified.)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
I_{QDD}	Quiescent V_{DD} Current	$V_{DD}=15\text{V}$, $V_{IN}=0\text{V}$ $V_{DD} - \text{COM}$	-	1.7	3.0	mA
I_{QBS}	Quiescent V_{BS} Current	$V_{BS}=15\text{V}$, $V_{IN}=0\text{V}$ $V_{B(X)}-V_{S(X)}$, $V_{B(V)}-V_{S(V)}$, $V_{B(W)}-V_{S(W)}$	-	45	70	μA
I_{PDD}	Operating V_{DD} Current	$V_{DD}=15\text{V}$, $F_{PWM}=20\text{kHz}$, duty=50%, PWM signal input for Low side $V_{DD} - \text{COM}$	-	1.9	3.2	mA
I_{PBS}	Operating V_{BS} Current	$V_{BS}=15\text{V}$, $F_{PWM}=20\text{kHz}$, duty=50%, PWM signal input for High side $V_{B(U)}-V_{S(U)}$, $V_{B(V)}-V_{S(V)}$, $V_{B(W)}-V_{S(W)}$	-	300	400	μA
UV_{DDD}	Low-side Undervoltage Protection (Figure 6)	V_{DD} Undervoltage Protection Detection Level	7.4	8.0	9.4	V
UV_{DDR}		V_{DD} Undervoltage Protection Reset Level	8.0	8.9	9.8	V
UV_{BSD}	High-side Undervoltage Protection (Figure 7)	V_{BS} Undervoltage Protection Detection Level	7.4	8.0	9.4	V
UV_{BSR}		V_{BS} Undervoltage Protection Reset Level	8.0	8.9	9.8	V
V_{TS}	HVIC Temperature sensing voltage output	$V_{DD}=15\text{V}$, $T_{HVIC}=25^\circ\text{C}$ (2nd Notes 3)	580	675	770	mV
V_{IH}	ON Threshold Voltage	Logic High Level	-	-	2.4	V
V_{IL}	OFF Threshold Voltage	Logic Low Level				
$V_{SC(ref)}$	SC Current Trip Level	$V_{DD}=15\text{V}$ $C_{SC} - \text{COM}$	0.45	0.5	0.55	V
t_{FOD}	Fault-out Pulse Width	$C_{FOD}=33\text{nF}$ (2nd Notes 4)	1.0	1.4	1.8	ms

2nd Notes:

- BV_{DSS} is the absolute maximum voltage rating between drain and source terminal of each MOSFET inside Motion SPM® 7 product. V_{PN} should be sufficiently less than this value considering the effect of the stray inductance so that V_{PN} should not exceed BV_{DSS} in any case.
- t_{ON} and t_{OFF} include the propagation delay of the internal drive IC. Listed values are measured at the laboratory test condition, and they can be different according to the field applications due to the effect of different printed circuit boards and wirings. Please see Figure 3 for the switching time definition with the switching test circuit of Figure 4.
- V_{TS} is only for sensing-temperature of module and cannot shutdown MOSFETs automatically.
- The fault-out pulse width t_{FOD} depends on the capacitance value of C_{FOD} according to the following approximate equation : $C_{FOD} = 24 \times 10^{-6} \times t_{FOD} [\text{F}]$

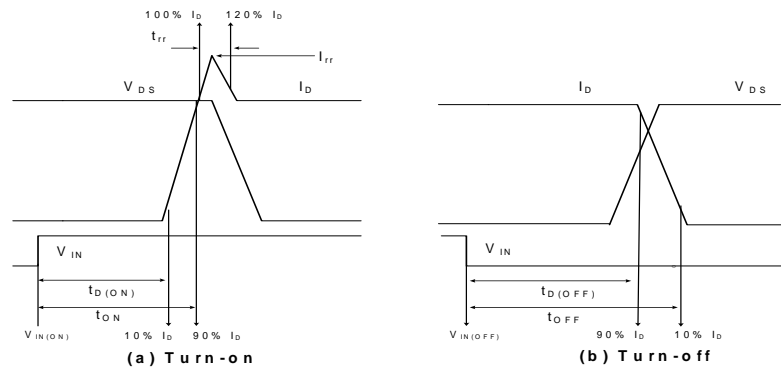


Figure 3. Switching Time Definition

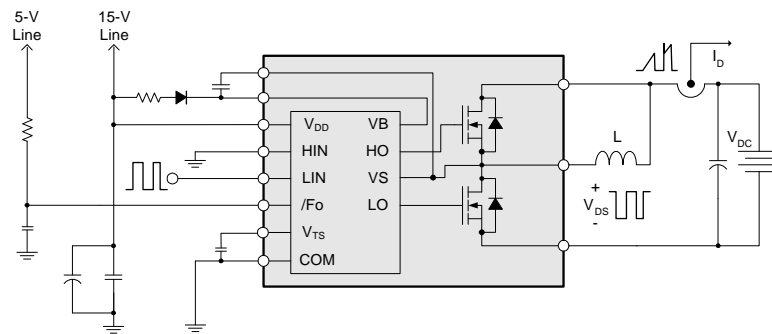


Figure 4. Switching Test Circuit (Low-side)

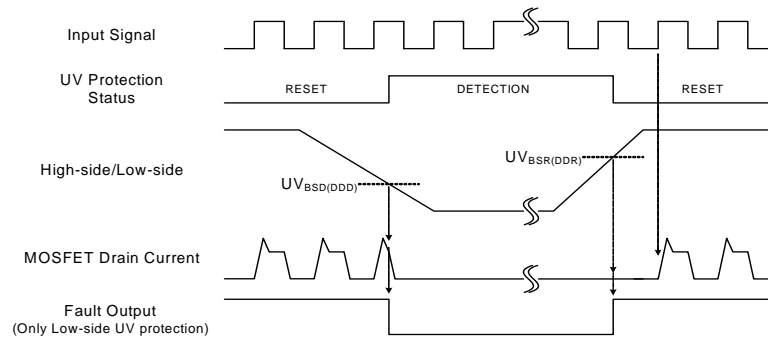


Figure 5. Under Voltage Protection

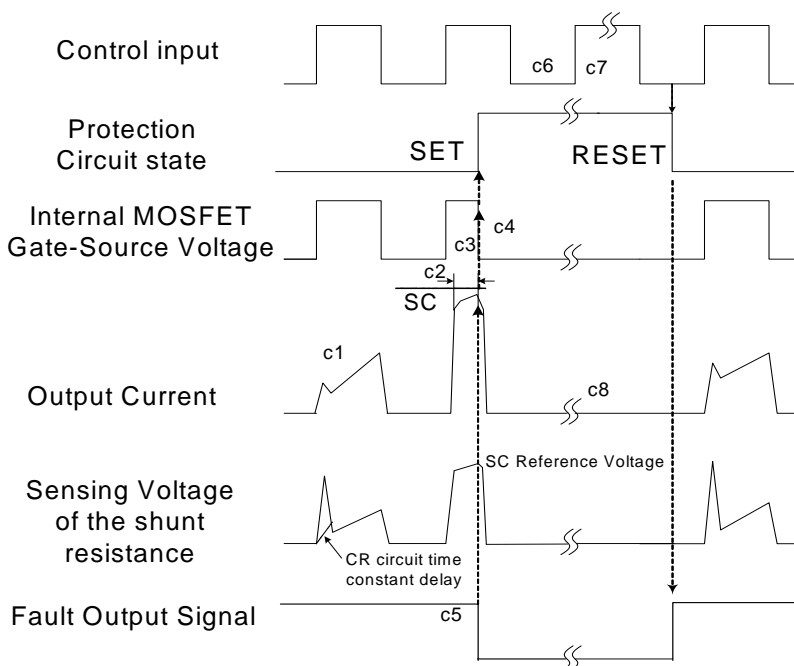


Figure 6. Short-Circuit Current Protection

(with the external shunt resistance and CR connection)

c1 : Normal operation: MOSFET ON and carrying current.

c2 : Short circuit current detection (SC trigger).

c3 : Hard MOSFET gate interrupt.

c4 : MOSFET turns OFF.

c5 : Fault output timer operation start : Fault-out width (t_{FOD})

c6 : Input "L" : MOSFET OFF state.

c7 : Input "H" : MOSFET ON state, but during the active period of fault output the MOSFET doesn't turn ON.

c8 : MOSFET OFF state

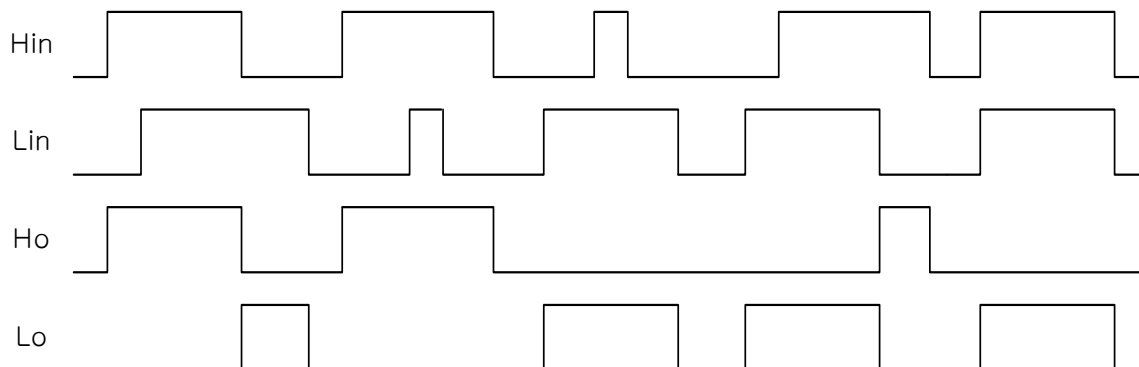


Figure 7. Timing Chart of Interlock Function

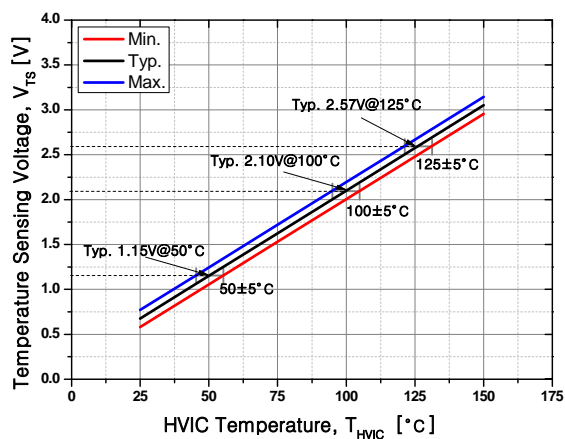


Figure 8. Temperature profile V_{TS} vs. T_{HVIC}

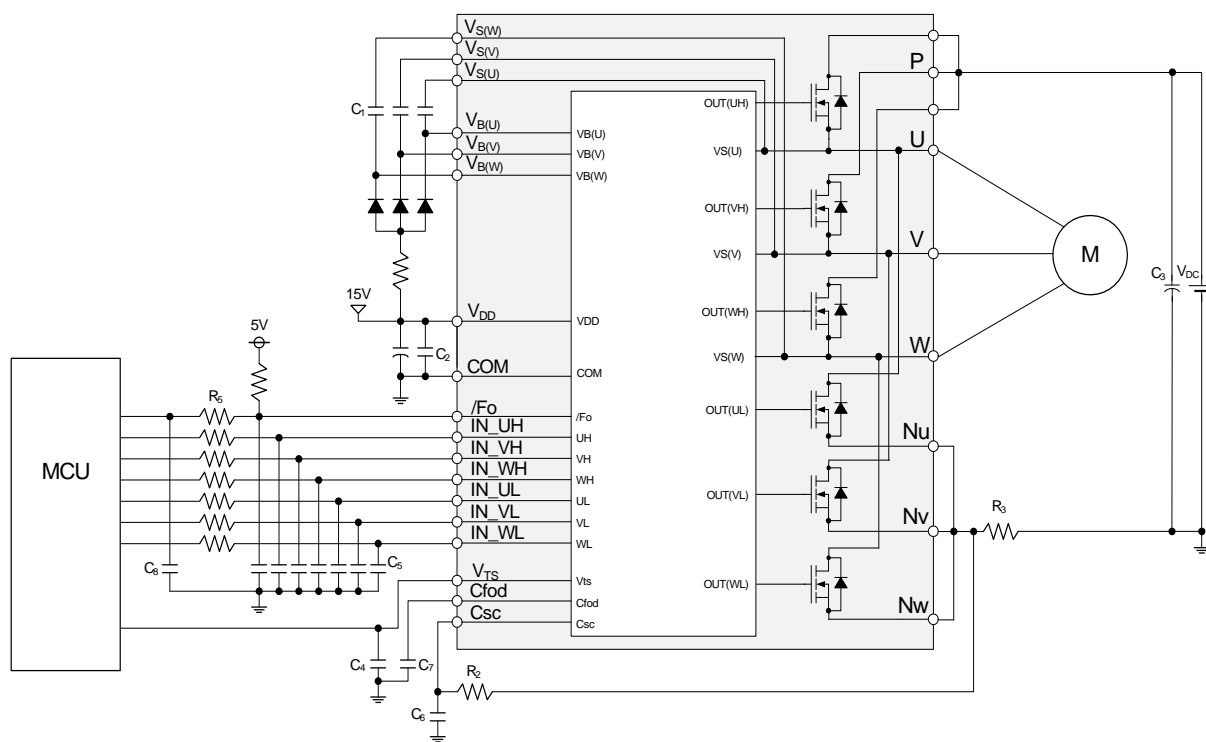
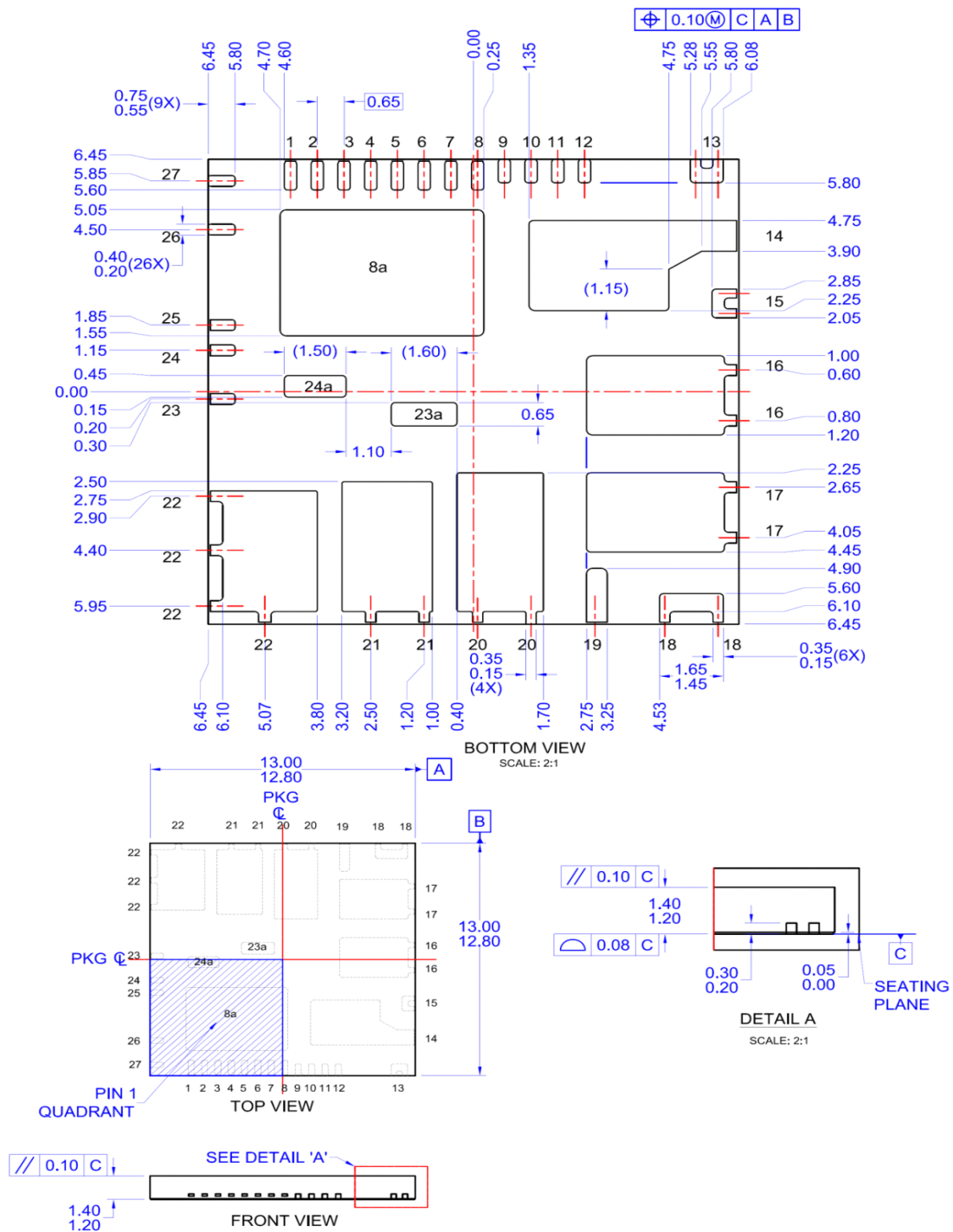


Figure 9. Example of Application Circuit

4th Notes:

1. RC-coupling (R_5 and C_5 , R_2 and C_6) and C_1 , C_5 , C_7 , C_8 at each input of Motion SPM® 7 product and MCU are useful to prevent improper input signal caused by surge-noise.
2. Ground-wires and output terminals, should be thick and short in order to avoid surge-voltage and malfunction of HVIC.
3. All the filter capacitors should be connected close to Motion SPM 7 product, and they should have good characteristics for rejecting high-frequency ripple current.

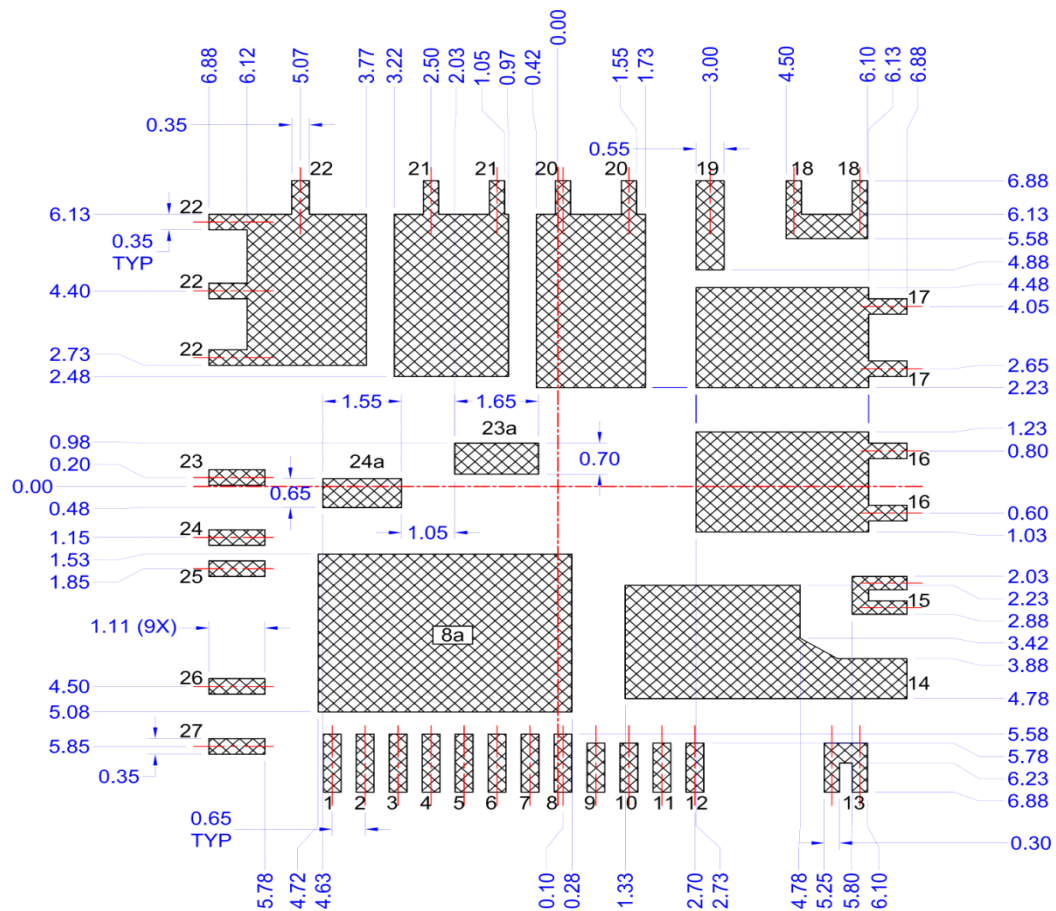
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LAND PATTERN
RECOMMENDATION
SCALE: 2:1

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- B) DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
- C) ALL DIMENSIONS ARE IN MILLIMETERS.
- D) DRAWING CONFORMS TO ASME Y14.5M-1994.
- E) LAND PATTERN REFERENCE:
QFN65P1290X1290X140-40N-40N
- F) DRAWING FILE NAME: MKT-PQFN27AREV3.
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